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	Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
	<u>"</u>	9599	((257/295) or (257/296) or (257/306) or (438/3) or (438/238) or (438/244)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 10:49
,	L2	7774	1 and @ad<"20030531"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 10:49
/	L3	138	2 and (ferroelectric PZT) and etch\$3 and ((therml\$2 heat\$3) near1 treat\$4) and (self-align\$4 selfalign\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 10:59
	L4	2	(ichimori near1 takashi).in. and (ferroelectric pzt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 11:01
/	L5	10	(ichimori near1 takashi).in. and (capacitor semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 11:11
	L6	14862	((438/3) or (438/238) or (438/239) or (438/24\$1) or (438/706) or (438/734) or (257/295) or (257/296) or (257/306)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 11:12
	L7	241	6 and @ad<"20030531" and (pzt ferroelectric) and etch\$3 and (((thermal\$2 heat\$3) near1 treat\$3) anneal\$3) and (self-align\$4 selfalign\$4) and capacitor and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 11:14
/	S1	3	"743073".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 10:48
	S2	180	(257/254).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:58
	S3	925	(257/734).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:58

	<b>S4</b>	0	S2 and S3	US-PGPUB; USPAT; EPO; JPO;	OR	OFF	2005/02/28 08:58
1				DERWENT; IBM_TDB			
	S5	570	(438/254).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:59
	S6	429	(438/734).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 08:59
,	S7	3	S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:05
	S8	1547	(438/3).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
	S9	1039	(438/197).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
j	S10	1060	(438/238).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
	S11	907	(438/239).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
	S12	1232	(438/240).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:05
	S13	2192	(438/253).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:06
	S14	1054	(438/706).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:06
	S15	7846	S5 S6 S8 S9 S10 S11 S12 S13 S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:28
/	S16	2688	S15 and (etching etchant etch) and (annealing anneal heat adj (treatment treating treated))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/02/28 10:14
,	S17	123	S16 and capacitor and second near3 (etching etch) near3 step	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/02/28 09:13

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′ S18	0	S17 and ferroeelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:14
) S19	97	S16 and capacitor and second near3 (etching etch) near3 step and (anneal annealing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:13
S20	35	S17 and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; ' IBM_TDB	OR	ON	2005/02/28 10:10
S21	6	S17 and ferroelectric and adhesion adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:12
S22	1	S17 and ferroelectric and adhesion adj layer near4 (etch etching etchant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:12
S23	742	S15 and (etching etchant etch) and (annealing anneal heat adj (treatment treating treated)) and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:14
S24	18	S15 and (etching etchant etch) and (annealing anneal heat adj (treatment treating treated)) and ferroelectric and (adhesion adhesive buffer) near2 (etch etching etchant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	<u>O</u> R	ON	2005/02/28 11:13
S25	2	jp-2001036026\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 11:16
/ S26	3	("6611014").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:17

;	S27	7	(US-20040238862-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20020074601-\$).did. or (US-6611014-\$).did. or (JP-2001036026-\$).did. or (JP-2001036026-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/02/28 15:31
	S28	5	barrier and S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 15:58
1	S29	35	oxygen adj barrier near6 lower adj electrode and capacitor and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF .	2005/02/28 15:58
,	S30	7	(US-20020074601-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$).did. or (US-6611014-\$).did. or (JP-2001036026-\$).did. or (JP-2001036026-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/01 06:59
:	S31	5	S30 and (Ir IrO iridium iridium adj oxide "Ir.sub."\$3"O")	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/01 08:09
,	S32	2	("6090443").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/01 08:14
	S33	0	("oxygenadjdiffusionandferroelectr icadjcapacitor").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/01 08:14
'	S34	171	oxygen adj diffusion and ferroelectric adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/01 08:15
,	S35	41	oxygen adj diffusion.ti,ab,clm. and ferroelectric adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/01 08:15

S36	27	oxygen adj diffusion.ti,ab,clm. and	US-PGPUB;	OR	ON	2005/03/01 08:15
, 330	27	ferroelectric adj capacitor.ti,ab, clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB		ON	. 2003/03/01 08.13
/ S37	28	(US-20020074601-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$ or US-20020137301-\$ or US-20020135067-\$),did. or (US-6611014-\$ or US-6090443-\$ or US-6613640-\$ or US-6566753-\$ or US-6479304-\$ or US-6399521-\$ or US-6236113-\$ or US-6146963-\$ or US-6072689-\$),did. or (EP-1054440-\$ or EP-1035589-\$ or EP-821415-\$),did. or (JP-2001036026-\$ or JP-2001118941-\$),did. or (JP-2001036026-\$ or US-20040195613-\$ or US-2004019670-\$ or US-20040004236-\$ or US-20040004236-\$ or US-20040004236-\$ or DE-10105997-\$ or EP-905786-\$), did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/01 08:32
, S38	28	(US-20020074601-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$ or US-20020137301-\$ or US-20020135067-\$).did. or (US-6611014-\$ or US-6090443-\$ or US-6613640-\$ or US-6566753-\$ or US-6479304-\$ or US-6399521-\$ or US-6236113-\$ or US-6146963-\$ or US-6072689-\$).did. or (EP-1054440-\$ or EP-1035589-\$ or EP-821415-\$).did. or (JP-2001036026-\$ or JP-2003273323-\$ or JP-2001118941-\$).did. or (JP-2001036026-\$ or US-20040195613-\$ or US-20040195613-\$ or US-20040129670-\$ or US-20040004236-\$ or DE-10105997-\$ or EP-905786-\$).	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/01 09:00
		DE-10105997-\$ or EP-905786-\$). did.		٠.		

S39	28	S38 and ferroelectric and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/01 09:01
S40	2	("20020074601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/25 14:53
S41	529	titanium adj oxide near4 insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/25 15:34
<sup>1</sup> S42	1266	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:36
S43	36	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2)) and ferroelectric. ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:38
S44	16	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2)) and ferroelectric. ti,ab,clm. and ("257"/\$7:ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:41
/ S45	4	((sputter\$3 deposit\$3) near3 (passivati\$2 encapsulati\$2)) same (etch\$3 near3 (passivati\$2 encapsulati\$2)) near6 ((lower bottom) near2 electrode) and ferroelectric.ti,ab,clm. and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:00
S46	0	(etch\$3 near3 (passivati\$2 encapsulati\$2)) near6 ((lower bottom) near2 electrode near8 self-align\$4) and ferroelectric.ti, ab,clm. and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:02
S47	7	(etch\$3 near5 (self-align\$4 selfalign\$4)) near5 ((bottom lower) adj electrode) and ferroelectric.ti,ab,clm.	US-PGPUB; ( USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:03

\$48 /	3	self-align\$4 near6 bottom adj electrode near6 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:36
S49	14	self-align\$4 near6 (lower bottom) adj electrode near6 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:37
/ S50	28	(US-20020074601-\$ or US-20020135067-\$ or US-20020137301-\$ or US-20020195633-\$ or US-20030211685-\$ or US-20040238862-\$).did. or (US-6072689-\$ or US-6090443-\$	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/26 10:41
<i>j</i>		or US-6146963-\$ or US-6236113-\$ or US-6399521-\$ or US-6479304-\$ or US-6566753-\$ or US-6611014-\$ or US-6613640-\$).did. or (EP-1035589-\$ or EP-1054440-\$ or EP-821415-\$).did. or (JP-2001036026-\$ or JP-2001118941-\$ or JP-2003273323-\$).did. or	7:12 years			
)		(EP-905786-\$ or JP-2001036026-\$ or DE-10105997-\$ or US-20040004236-\$ or US-20040129670-\$ or US-20040180453-\$ or US-20040195613-\$).did.	and the second second			
S51	4	S50 and resist near4 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:01
S52	2	("20020074601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:01
S53	2	S50 and hard adj mask near10 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF.	2005/07/26 12:01

	S54	2536	438/3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
,	S55	2337	438/197	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
	S56	2477	438/238	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
<i>y</i>	S57	155467	"438"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 12:29
,	S58	7777	((438/239) or (438/240) or (438/253) or (438/254) or (438/706) or (438/734) or (438/197)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/26 12:31
	S59	65	S58 and (feRAM ferroelectric).ti, ab,clm. and semiconductor and etch\$3 and hard adj mask and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 12:32
1	S60	3	"743073".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/23 15:20
	S61	1	(US-20040238862-\$).did.	US-PGPUB	OR	OFF	2005/12/23 15:21
	S62	1	S61 and (self-align\$4 self adj align\$4 slefalign\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/23 15:47
	S63	2	("20020074601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/23 15:53

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,	S64	1	S63 and (hard adj mask mask)	US-PGPUB; ( USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/23 15:55
	S65	3	("6611014").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/23:15:56
,	S66	. 1	S65 and (hard adj mask mask masking)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 17:12
	S67	1	S65 and (self-align\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 17:28
)	S68	0	S65 and (self-align\$4) near10 (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 17:28
,	S69	i	S65 and (self-align\$4) and (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/12/23 17:38
-	S70	28	self-align\$4 near6 capacitor near6 ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 17:40
,	S71	28	self-align\$4 near6 capacitor near6 ferroelectric and self-align\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/12/23 18:16
	S72	6997	((438/3) or (438/238) or (438/239) or (438/240) or (438/253) or (438/254) or (438/703) or (438/734)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/12/23 18:17
	S73	1	S72 and (self-align\$4 "self" adj align\$4).ti,ab,clm. and ferroelectric.ti,ab,clm. and hard adj mask.ti,ab,clm. and (anneal\$3 heat thermal).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	°2005/12/23 18:18

/ Sī	74	2	("20020074601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:38
S.	75	3	multi-layered adj encapsulation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:39
S	76	3	(multi-layered multilayered) adj encapsulation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:39
s:	77	3	(multi-layered multilayered double) adj encapsulation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:40
S	78	3	(multi-layered multilayered double triple) adj encapsulation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:40
, S	79	3	(multi-layered multilayered double triple laminated) adj encapsulation adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:40
SS J	80	91	(multi-layered multilayered double triple laminated) adj encapsulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 17:41
S	81	21	(multi-layered multilayered double triple laminated) adj encapsulation ti,ab,cim.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 17:41
S	82	0	(multi-layered multilayered double triple laminated) adj encapsulation.ti,ab,clm. and memory and pzt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 17:41
SE /	83	1	(multi-layered multilayered double triple laminated) adj encapsulation:ti;ab;clm. and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 17:42

S84	2	("6740531").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:46
S85	0	("ferroelectricnear4pzt").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:46
S86	2768	ferroelectric near4 pzt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 17:46
S87	1	(US-20040238862-\$).did.	US-PGPUB	OR	OFF	2006/06/10 21:45
S88	1	S87 and contact adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 21:49
S89	1	S87 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 22:13
S90	. 22	"6611014"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 22:15
S91	5	"602764".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/10 22:15
S92	1	(US-20040238862-\$).did.	US-PGPUB	OR	OFF	2006/06/11 08:38
S93	22	"6611014"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 08:39
S94	2	("6661014").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 08:39

S95	3	("6611014").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 08:53
. S96	2	("20020021544").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/11 08:54
S97	1	S96 and insulati\$2 near6 (hydrogen adj diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:55
S98	1	S96 and insulati\$2 near6 (hydrogen adj diffusion) and (first second) adj insulati\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:55